



# BZ1,BZ2,BZ3,BZ4

## GLASS PASSIVATED SILICON RECTIFIER DIODE

### Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.
7. Implementation of standards: GJB33A-97, QZJ840611A, QZJ840611



### TECHNICAL DATA:

(Ta = 25°C )

Parameter name	Symbols	Unit	Specifications				Test Condition
			BZ1	BZ2	BZ3	BZ4	
Use for	Industrial frequency rectifier circuit.						
Store temperature	T	°C	-55~+150				
Quality Class	JP, JT, JCT, GS, G, G+						
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	V	50~1400				
Average Forward Current	I <sub>F(AV)</sub>	A	1.0	1.5	2.0	3.0	
Peak Forward Voltage	V <sub>FM</sub>	V	2.2	2.2	2.4	A~F:2.2 G~J:2.6	I=I <sub>F(AV)</sub>
Average Forward Voltage	V <sub>F</sub>	V	1.0	1.0	1.2	A~F:1.2 G~J:1.5	I=I <sub>F(AV)</sub>
Non-repeat Forward Surge Current	I <sub>FSM</sub>	A	20	30	40	50	Single-phase industrial frequency sine half wave 10ms
Peak Reverse Current	I <sub>RM1</sub>	uA	10				V <sub>R</sub> =V <sub>RRM</sub> , Ta=25°C
Peak Reverse Current	I <sub>RM2</sub>	uA	200				V <sub>R</sub> =V <sub>RRM</sub> , Ta=125°C
Junction Temperature	T <sub>jm</sub>	°C	150				

### SPECIFICATIONS:

A	B	C	D	E	F	G	H	I	J
50V	100V	200V	300V	400V	600V	800V	1000V	1200V	1400V

### Outline and Dimensions:

Model Cross: BZ4(2CZ5550)